





## 246NQ200/R-1 SCHOTTKY RECTIFIER



### **Features**

- 175℃ T<sub>J</sub> operation
- Unique high power, Half-Pak module
- Replaces three parallel DO-5'S
- Easier to mount and lower profile than DO-5' S
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Very low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- Base plate: Nickel plated; Terminals: Nickel plated
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

## **Circuit Diagram**



#### 246NQ200R-1

The top side is terminal, the bottom side is base plate.

### **Applications**

- Switching power supply
- Converters
- Free-Wheeling diodes
- **Reverse battery protection**

### **Maximum Ratings:**

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	-	200	V
Average Forward Current	I <sub>F(AV)</sub>	50% duty cycle @T <sub>C</sub> =110°C, rectangular wave form	240	А
Peak One Cycle Non-Repetitive Surge Current	I <sub>FSM</sub>	8.3 ms, half Sine pulse	3950	Α

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## **Electrical Characteristics:**

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop*	V <sub>F1</sub>	@ 240A, Pulse, T <sub>J</sub> = 25 °C	0.88	1.12	V
	$V_{F2}$	@ 240A, Pulse, T <sub>J</sub> = 125 °C	0.77	0.79	V
Reverse Current*	I <sub>R1</sub>	$@V_R = \text{rated } V_R T_J = 25 ^{\circ}\text{C}$	0.0004	6	mA
	I <sub>R2</sub>	$@V_R = \text{rated } V_R T_J = 125  ^{\circ}\text{C}$	0.3	85	mA
Junction Capacitance	Ст	$@V_R = 5V, T_C = 25 °C$ $f_{SIG} = 1MHz$	3000	3600	pF
Voltage Rate of Change	dv/dt	-	-	10,000	V/μs

 $<sup>^{\</sup>star}\,$  Pulse width < 300  $\mu s,\,$  duty cycle < 2%

# **Thermal-Mechanical Specifications:**

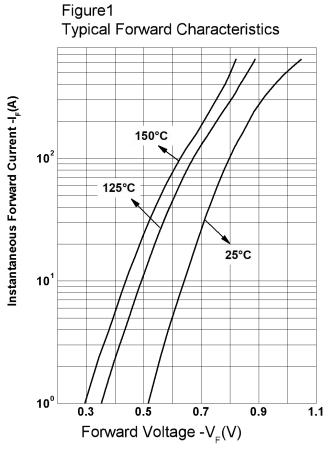
Characteristics	Symbol	Condition	Specification		Units
Junction Temperature	ΤJ	-	-55 to +175		°C
Storage Temperature	$T_{stg}$	-	-55 to +175		°C
Typical Thermal Resistance Junction to Case	$R_{ heta JC}$	DC operation	0.25		°C/W
Typical Thermal Resistance, case to Heat Sink	R <sub>θcs</sub>	Mounting surface, smooth and greased	0.07		°C/W
Mounting Torque	T <sub>M</sub>	Non-lubricated threads	Mounting Torque	23(min) 29(max)	Va om
			Terminal Torque	35(min) 46(max)	- Kg-cm
Approximate Weight	wt	-	36		g
Case Style	PRM1-1				

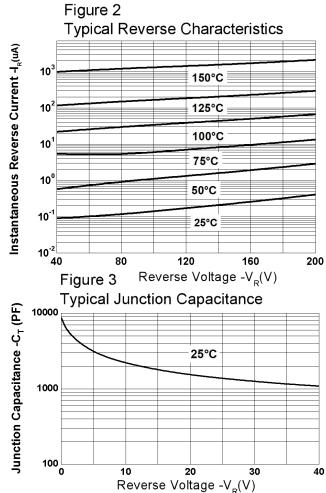






## **Ratings and Characteristics Curves**





## **Ordering Information**

Device	Package	Shipping	
246NQ200-1	PRM1-1(Pb-Free)	27pcs/ box	

## **Marking Diagram**



Where XXXX is YYWW

1st row SS YYWW
2nd row 246NQ200-1
SS = SS
YY = Year
WW = Week

Cautions: Molding resin Epoxy resin UL:94V-0

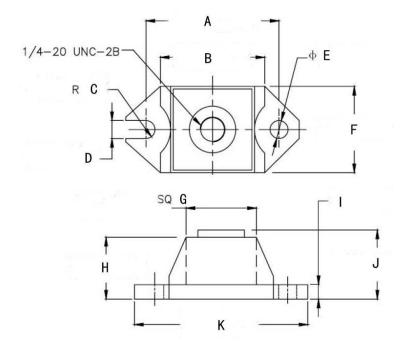
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# **Mechanical Dimensions PRM1-1 (Inches/Millimeters)**



SYMBOL	Millimeters		Inches		
	Min.	Max.	Min.	Max.	
Α	29.35	30.95	1.155	1.219	
В	24.77	26.04	0.975	1.026	
С	1.79	2.19	0.070	0.087	
D	3.73	4.24	0.146	0.167	
E	3.73	4.24	0.146	0.167	
F	18.42	19.69	0.725	0.775	
G	18.55	19.55	0.730	0.770	
Н	13.59	14.47	0.535	70.500	
I	3.05	3.90	0.120	0.154	
J	14.87	15.87	0.585	0.625	
K	38.61	39.62	1.520	1.560	







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